

General Description

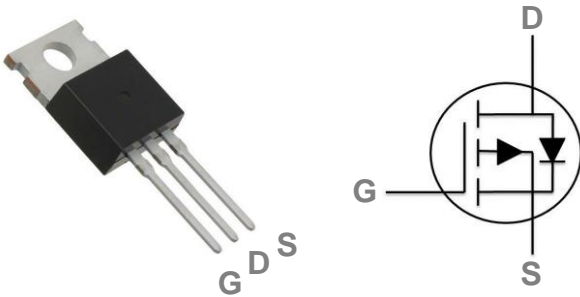
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	R _{DS(ON)}	ID
-100V	45mΩ	-35A

Features

- -100V, -35A, R_{DS(ON)} 45mΩ@V_{GS} = -10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

TO220 Pin Configuration



Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _c =25°C)	-35	A
	Drain Current – Continuous (T _c =100°C)	-22	A
I _{DM}	Drain Current – Pulsed ¹	-140	A
EAS	Single Pulse Avalanche Energy ²	180	mJ
IAS	Single Pulse Avalanche Current ²	-60	A
P _D	Power Dissipation (T _c =25°C)	114	W
	Power Dissipation – Derate above 25°C	0.91	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJC}	Thermal Resistance Junction to Case	---	1.1	°C/W
R _{θJA}	Thermal Resistance Junction to ambient	---	62	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-100	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-80V, V _{GS} =0V, T _J =85°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-15A	---	36	45	mΩ
		V _{GS} =-4.5V, I _D =-10A	---	40	55	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	---	-2.5	V
g _{fs}	Forward Transconductance	V _{DS} =-10V, I _D =-5A	---	22	---	S

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3,4}	V _{DS} =-50V, V _{GS} =-10V, I _D =-10A	---	98	150	nC
Q _{gs}	Gate-Source Charge ^{3,4}		---	16.2	30	
Q _{gd}	Gate-Drain Charge ^{3,4}		---	13.8	26	
T _{d(on)}	Turn-On Delay Time ^{3,4}	V _{DD} =-50V, V _{GS} =-10V, R _G =25Ω I _D =-5A	---	58	105	ns
T _r	Rise Time ^{3,4}		---	24	50	
T _{d(off)}	Turn-Off Delay Time ^{3,4}		---	215	450	
T _f	Fall Time ^{3,4}		---	94	180	
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, F=1MHz	---	6315	9000	pF
C _{oss}	Output Capacitance		---	220	330	
C _{rss}	Reverse Transfer Capacitance		---	50	100	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-35	A
I _{SM}	Pulsed Source Current		---	---	-70	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=-50V, V_{GS}=-10V, L=0.1mH, I_{AS}=-60A., Starting T_J=25°C
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

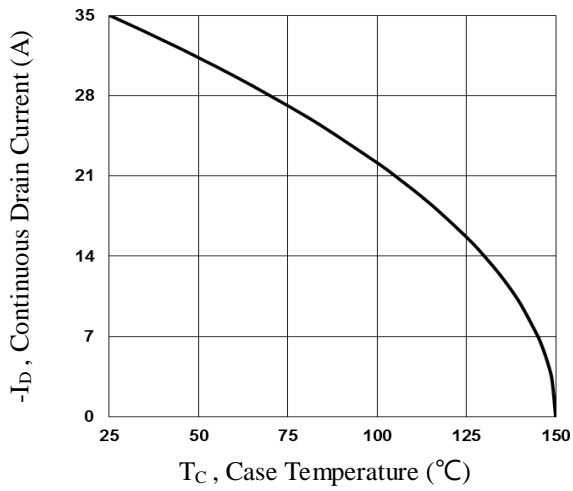


Fig.1 Continuous Drain Current vs. T_c

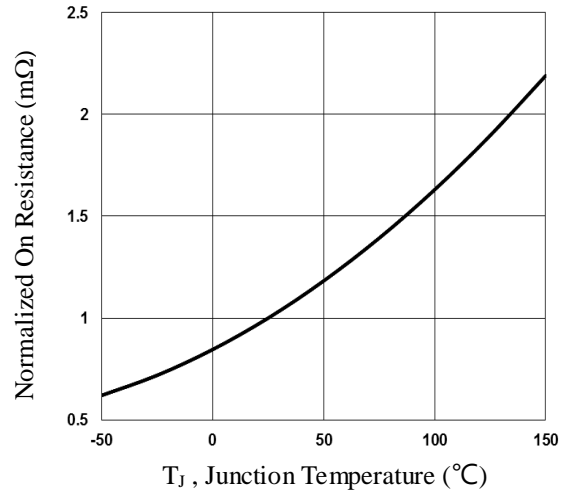


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

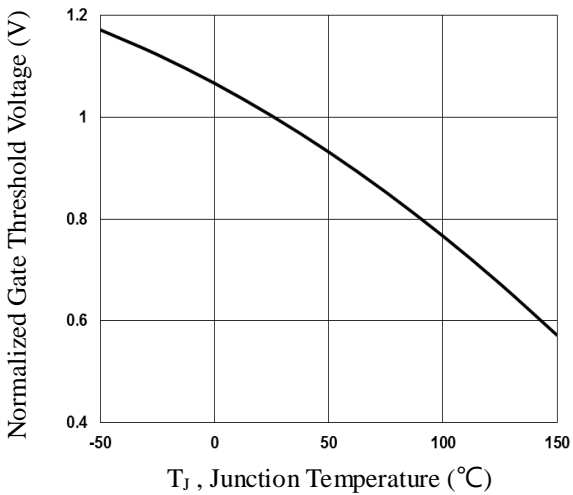


Fig.3 Normalized V_{th} vs. T_j

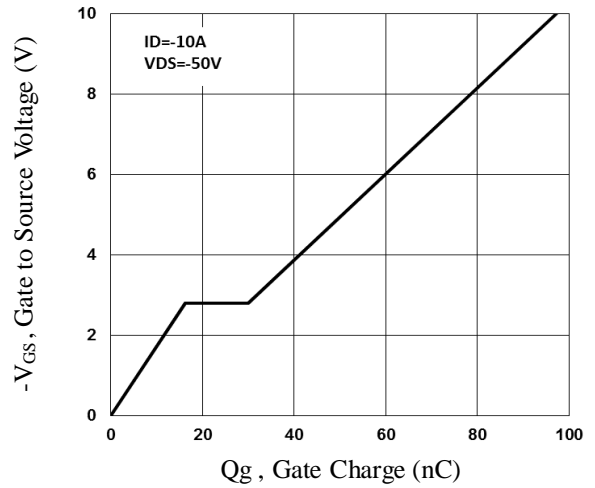


Fig.4 Gate Charge Waveform

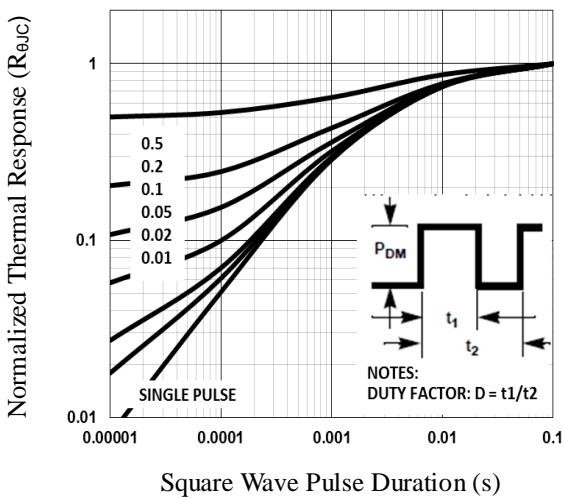


Fig.5 Normalized Transient Impedance

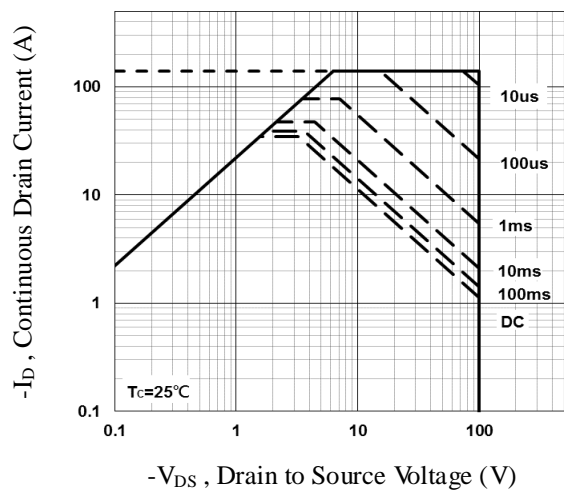


Fig.6 Maximum Safe Operation Area

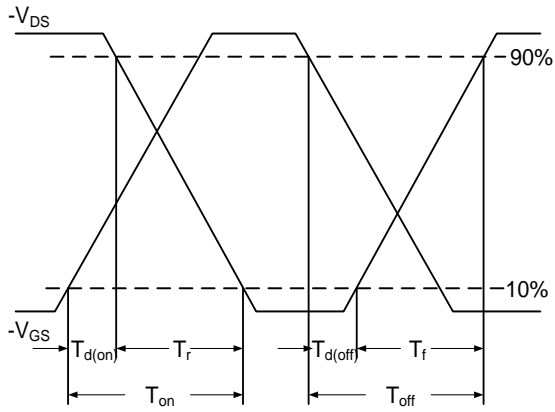


Fig.7 Switching Time Waveform

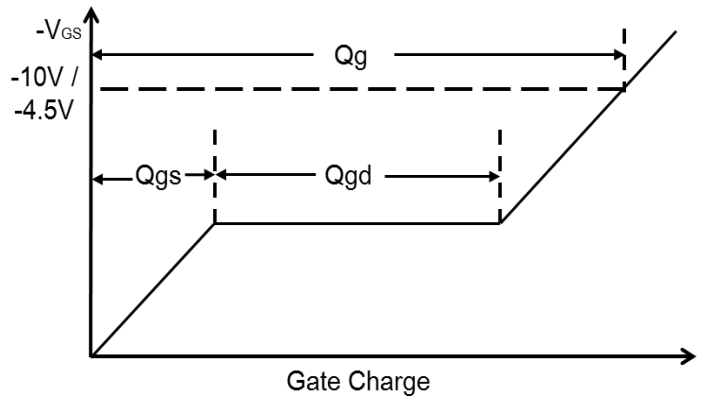
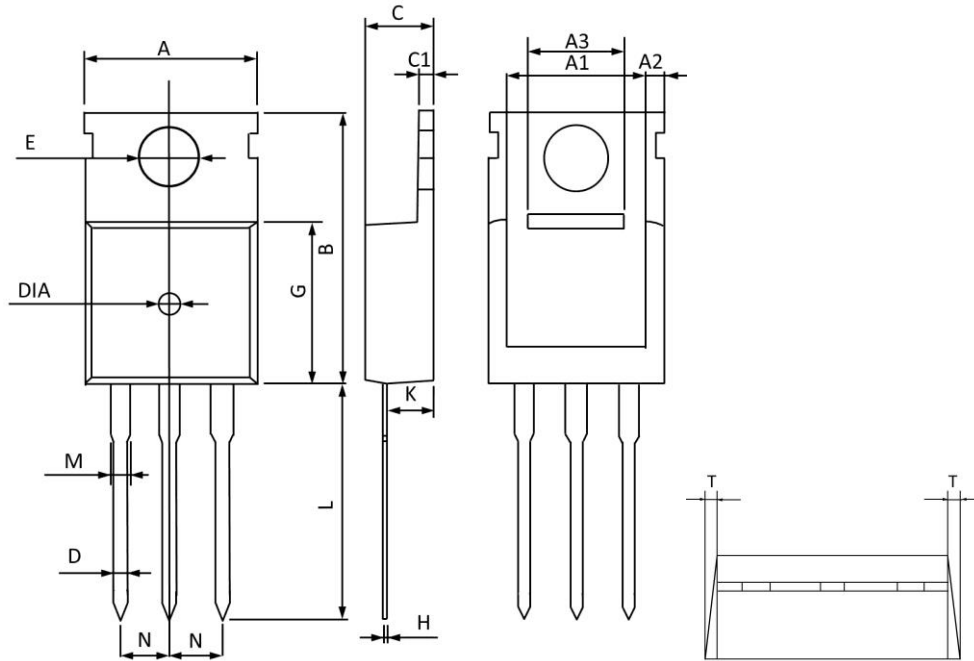


Fig.8 Gate Charge Waveform

TO220 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	10.300	9.700	0.406	0.382
A1	8.840	8.440	0.348	0.332
A2	1.250	1.050	0.049	0.041
A3	5.300	5.100	0.209	0.201
B	16.200	15.400	0.638	0.606
C	4.680	4.280	0.184	0.169
C1	1.500	1.100	0.059	0.043
D	1.000	0.600	0.039	0.024
E	3.800	3.400	0.150	0.134
G	9.300	8.700	0.366	0.343
H	0.600	0.400	0.024	0.016
K	2.700	2.100	0.106	0.083
L	13.600	12.800	0.535	0.504
M	1.500	1.100	0.059	0.043
N	2.590	2.490	0.102	0.098
T	W0.35		W0.014	
DIA	Φ1.5 TYP.	deep0.2 TYP.	Φ0.059 TYP.	deep0.008 TYP.